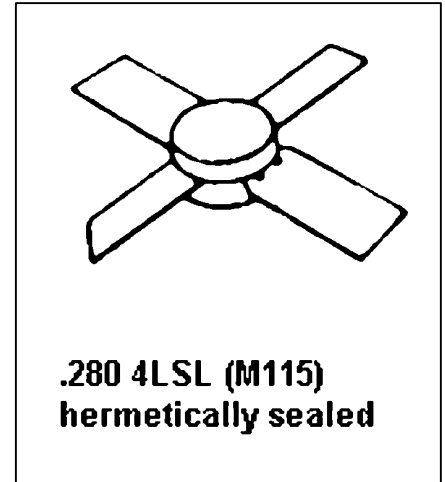
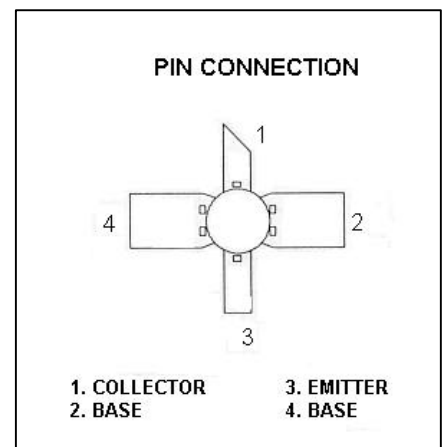


SD1536-03
**RF & MICROWAVE TRANSISTORS
 AVIONICS APPLICATIONS**
Features

- 1025 – 1150 MHz
- 50 VOLTS
- P_{OUT} = 90 W
- G_p = 8.4 dB MINIMUM
- INPUT MATCHED
- COMMON BASE CONFIGURATION


DESCRIPTION:

The SD1536-03 is a gold metallized silicon NPN power transistor designed for applications requiring high peak power and low duty cycles such as IFF, DME and TACAN. Internal Impedance matching provides improved broadband performance.


ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector – Base Voltage	65	V
V _{CES}	Collector – Emitter Voltage	65	V
V _{EBO}	Emitter – Base Voltage	3.5	V
I _C	Device Current	10	A
P _{DISS}	Power Dissipation	292	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

R _{TH(J-C)}	Junction-Case Thermal Resistance	0.60	°C/W
----------------------	----------------------------------	------	------

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)
STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	I_C = 10 mA	I_E = 0 mA	65	---	---	V
BV_{CER}	I_C = 25 mA	R_{BE} = 10 Ω	65	---	---	V
BV_{EBO}	I_E = 1 mA	I_C = 0 mA	3.5	---	---	V
I_{CES}	V_{CE} = 50 V	I_E = 0 mA	---	---	10	mA
h_{FE}	V_{CE} = 5 V	I_C = 100 mA	5	---	---	---

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	f = 1025 - 1150MHz	P_{IN} = 13.0 W	V_{CE} = 50 V	90	---	---	W
G_P	f = 1025 - 1150MHz	P_{IN} = 13.0 W	V_{CE} = 50 V	8.4	---	---	dB

Conditions: Pulse Width = 10 μSec, Duty Cycle = 1%
 This device is suitable for use under other pulse width/duty cycle conditions.
 Please contact the factory for specific applications assistance.

IMPEDANCE DATA

FREQ	Z _{IN} (Ω)	Z _{CL} (Ω)
960 MHz	2.5 + j13.0	4.6 – j5.5
1030 MHz	5.2 + j15.0	5.0 – j5.5
1090 MHz	16.3 + j15.0	4.8 – j5.5
1150 MHz	14.7 + j2.5	4.7 – j7.0
1215 MHz	7.6 + j0.5	4.7 – j5.0

P_{IN} = 13W
V_{CE} = 50 V

PACKAGE MECHANICAL DATA

